

SCDS253-SEPTEMBER 2007

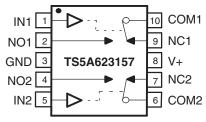
FEATURES

- Overshoot and Undershoot Voltage Protection
- Specified Break-Before-Make Switching
- Low ON-State Resistance (10 Ω)
- Control Inputs Are 5-V Tolerant
- Low Charge Injection
- Excellent ON-Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.8-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)
 - 300-V Machine Model (A115-A)

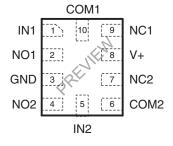
APPLICATIONS

- Sample-and-Hold Circuit
- Battery-Powered Equipments
- Audio and Video Signal Routing
- Communication Circuits

DGS PACKAGE (TOP VIEW)



RSE PACKAGE (TOP VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS5A623157 is a dual single-pole, double-throw (SPDT) analog switch designed to operate from 1.65 V to 5.5 V. This device can handle both digital and analog signals. Signals up to V+ (peak) can be transmitted in either direction.

The TS5A623157 senses overshoot and undershoot events at the I/Os and responds by preventing voltage differentials from developing and turning the switch on.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾	(2)	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
–40°C to 85°C	VSSOP (MSOP-10) - DGS	Tape and reel	TS5A623157DGSR	35R	
-40 C to 65 C	QFN - RSE	Tape and reel	TS5A623157RSER	PREVIEW	

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

FUNCTION TABLE

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCT PREVIEW

SUMMARY OF CHARACTERISTICS $V_{+} = 5 \text{ V}, T_{A} = 25^{\circ}\text{C}$

Configuration	2:1 multiplexer/demultiplexer (1 × SPDT)
Number of channels	2
ON-state resistance (r _{on})	10 Ω
ON-state resistance match (Δr _{on})	0.15 Ω
ON-state resistance flatness (r _{on(flat)})	2 Ω
Turn-on/turn-off time (t _{ON} /t _{OFF})	5 ns / 3.4 ns
Break-before-make time (t _{BBM})	0.5 ns
Charge injection (Q _C)	5 pC
Bandwidth (BW)	371 MHz
OFF isolation (O _{ISO})	-61 dB at 10 MHz
Crosstalk (X _{TALK})	–61 dB at 10 MHz
Total harmonic distortion (THD)	0.06%
Leakage current (I _{NO(OFF)} /I _{NC(OFF)})	±1 μA
Power-supply current (I ₊)	1.2 μΑ
Undershoot protection	–2 V
Overshoot protection	V ₊ + 2 V
Package options	10-pin VSSOP (DGS), 10-pin QFN (RSE)

Absolute Minimum and Maximum Ratings (1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V+	Supply voltage range ⁽³⁾		-0.5	6.5	V
V _{NC} V _{NO} V _{COM}	Analog voltage range ⁽³⁾⁽⁴⁾⁽⁵⁾		-0.5	V ₊ + 0.5	V
I _{I/OK}	Analog port diode current	$V+ < V_{NC}, V_{NO}, V_{COM} < 0$		±50	mA
I _{NC} I _{NO} I _{COM}	On-state switch current		±50	mA	
V_{IN}	Digital input voltage range (3)(4)		-0.5	6.5	V
I_{IK}	Digital input clamp current	V ₁ < 0		-50	mA
I+ I _{GND}	Continuous current through V ₊ or GND		±100	mA	
T _{stg}	Storage temperature range		-65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.

Package Thermal Impedance

				UNIT
θ_{JA}	Package thermal impedance ⁽¹⁾	DGS package	165	°C/W
	Package thermal impedance **	RSE package	243	C/VV

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

PRODUCT PREVIEV

Electrical Characteristics for 5-V Supply

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Analog Switch					1			- 1	
Analog signal range	$V_{\text{COM}}, V_{\text{NO}}, V_{\text{NC}}$					0		V ₊	V
Voltage undershoot	V _{IKU}	$0 \ge (I_{NC}, I_{NO}, \text{ or } I_{COM}) \ge$	–50 mA		5.5 V			-2	V
Peak ON-state resistance	r _{peak}	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -30 \text{ mA},$	Switch ON, See Figure 14	25°C Full	4.5 V		4.6	11 13	Ω
		V_{NO} or $V_{NC} = 0$,		25°C			4	6.5	
		I _{COM} = 30 mA		Full				8	
ON-state	_	V_{NO} or $V_{NC} = 2.4 \text{ V}$,	Switch ON,	25°C	451/		4	8	0
resistance	r _{on}	$I_{COM} = -30 \text{ mA}$	See Figure 14	Full	4.5 V			10	Ω
		V_{NO} or $V_{NC} = 4.5 \text{ V}$,		25°C			5.5	10	
		$I_{COM} = -30 \text{ mA}$		Full				12	
ON-state				25°C			0.1	0.14	
resistance match between channels	Δr _{on}	V_{NO} or $V_{NC} = 3.15 \text{ V}$, $I_{COM} = -30 \text{ mA}$,	Switch ON, See Figure 14	Full	4.5 V			0.15	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			1.5	2	
resistance flatness	r _{on(flat)}	$I_{COM} = -30 \text{ mA},$	See Figure 14	Full	4.5 V			4	Ω
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0$ to V_{+}	Switch OFF,	25°C			1	20	
OFF leakage current	I _{NO(OFF)}	$V_{COM} = V_+ \text{ to } 0$	See Figure 15	Full	5.5 V			150	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0$ to V_+	Switch ON,	25°C			1	20	
ON leakage current	I _{NO(ON)}	$V_{COM} = Open,$	See Figure 16	Full	5.5 V			150	nA
COM		V_{NC} or V_{NO} = Open,	Switch ON,	25°C			1	20	
ON leakage current	I _{COM(ON)}	$V_{COM} = 0$ to V_+ ,	See Figure 16	Full	5.5 V			150	nA
Digital Control II	nput (IN)								
Input logic high	V _{IH}			Full		$V_+ \times 0.7$		5.5	V
Input logic low	V _{IL}			Full		0		$V_{+} \times 0.3$	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	5.5 V		0.1	10 30	nA



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Electrical Characteristics for 5-V Supply (continued)

 V_{+} = 4.5 V to 5.5 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	ETER SYMBOL TEST CONDITIONS T _A V ₊		V ₊	MIN	TYP	MAX	UNIT		
Dynamic									
		V - V or CND	C _L = 50 pF,	25°C	5 V	1	3.5	5	
Turn-on time	t _{ON}	$V_{COM} = V_{+} \text{ or GND},$ $R_{L} = 500 \Omega,$	See Figure 17	Full	4.5 V to 5.5 V	1		6	ns
		V OND	0 50 5	25°C	5 V	1	2.8	3.4	
Turn-off time	t _{OFF}	$V_{COM} = V_{+} \text{ or GND},$ $R_{L} = 500 \Omega,$	C _L = 50 pF, See Figure 17	Full	4.5 V to 5.5 V	1		3.8	ns
Output voltage during undershoot	V _{OUTU}	See Figure 24				2.5	V _{OH} – 0.3		V
Output voltage during overshoot	V _{OUTO}	See Figure 24					V _{OL} + 0.3	2	V
Prook before		V - V - V /2	C = 50 pE	25°C	5 V	0.5	5	12	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2,$ $R_{L} = 50 \Omega,$	C _L = 50 pF, See Figure 18	Full	4.5 V to 5.5 V	0.5		14	ns
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 0.1 nF, See Figure 22	25°C	5 V		110		рС
NC, NO OFF capacitance	$C_{NC(OFF)}, \ C_{NO(OFF)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	5 V		5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 16	25°C	5 V		14.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	5 V		14.5		pF
Digital input capacitance	C _I	$V_I = V_+$ or GND,	See Figure 16	25°C	5 V		3.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	5 V		371		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 10 MHz,	Switch OFF, See Figure 20	25°C	5 V		-61		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 10 MHz,	Switch ON, See Figure 21	25°C	5 V		-61		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	5 V		0.06		%
Supply									
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	5.5 V		0.01	0.15	μΑ

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Electrical Characteristics for 3.3-V Supply

 $V_{\scriptscriptstyle +}$ = 3 V to 3.6 V, T_{A} = $-40^{\circ} C$ to $85^{\circ} C$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	$V_{\text{COM}}, V_{\text{NO}}, V_{\text{NO}}$					0		V ₊	V
Voltage undershoot	V_{IKU}	$0 \ge (I_{NC}, I_{NO}, \text{ or } I_{COM}) \ge$	–50 mA		3.6 V				V
Peak ON-state	r .	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	3 V		8.9	14	Ω
resistance	r _{peak}	$I_{COM} = -24 \text{ mA},$	See Figure 14	Full	3 V			18	32
		V_{NO} or $V_{NC} = 0$,		25°C			5.4	8	
ON-state	r _{on}	I _{COM} = 24 mA Switch ON,		Full	3 V			10	Ω
resistance	ion	V_{NO} or $V_{NC} = 3 V$,	See Figure 14	25°C			7.4	12	32
		I _{COM} = -24 mA		Full				15	
ON-state resistance				25°C			0.1	0.2	
match between channels	Δr_{on}	V_{NO} or $V_{NC} = 2.1 \text{ V}$, $I_{COM} = -24 \text{ mA}$,	Switch ON, See Figure 14		Full 3 V			0.2	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			2.8	4	
resistance flatness	r _{on(flat)}	$I_{COM} = -24 \text{ mA},$	See Figure 14	Full	3 V			7	Ω
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0$ to V_{+}	Switch OFF,	25°C	0.01/		0.5	10	
OFF leakage current	I _{NO(OFF)}	$V_{COM} = V_{+}$ to 0	See Figure 15	Full	3.6 V			100	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0$ to V_{+}	Switch ON.	25°C	0.01/		0.5	10	
ON leakage current	I _{NO(ON)}	V _{COM} = Open,	See Figure 16	Full	3.6 V			100	nA
COM		V_{NC} or V_{NO} = Open,	Switch ON,	25°C			0.5	10	_
ON leakage current	I _{COM(ON)}	$V_{COM} = 0$ to V_+ ,	See Figure 16	Full	3.6 V			100	nA
Digital Control II	nput (IN)								
Input logic high	V_{IH}			Full		$V_+ \times 0.7$		5.5	V
Input logic low	V_{IL}			Full		0		$V_{+} \times 0.3$	V
Input leakage	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	°C 3.6 V		0.1	10	nA
current	ווי יוווי.	V ₁ = 3.5 V 01 0		Full	0.0 v			20	11/ \

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Electrical Characteristics for 3.3-V Supply (continued)

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CON	TEST CONDITIONS TA V+ MIN TYP MAX U		UNIT				
Dynamic								'	
		$V_{COM} = V_{+} \text{ or GND},$	C _L = 50 pF,	25°C	3.3 V	1	4.7	9.0	
Turn-on time	t _{ON}	$R_L = 500 \Omega$	See Figure 17	Full	3 V to 3.6 V	1		10.0	ns
		V or CND	C	25°C	3.3 V	1	3.2	6.3	
Turn-off time	t _{OFF}	$V_{COM} = V_{+} \text{ or GND},$ $R_{L} = 500 \Omega,$	C _L = 50 pF, See Figure 17	Full	3 V to 3.6 V	1		7.0	ns
Output voltage during undershoot	V _{OUTU}	See Figure 24				2.5	V _{OH} – 0.3		V
Output voltage during overshoot	V _{OUTO}	See Figure 24					V _{OL} + 0.3	2	V
Break-before-		V - V - V /2	$C_1 = 50 \text{ pF},$	25°C	3.3 V	0.5	7	17	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2,$ $R_{L} = 50 \Omega,$	See Figure 18	Full	3 V to 3.6 V	0.5		19.5	ns
Charge injection	Q _C	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 0.1 \text{ nF},$ See Figure 22	25°C	3.3 V		75		рС
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V _{NC} or V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		5		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V _{NC} or V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		14.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		14.5		pF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	3.3 V		3.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	3.3 V		370		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 10 MHz,	Switch OFF, See Figure 20	25°C	3.3 V		-60		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 10 MHz$,	Switch ON, See Figure 21	25°C	3.3 V		-60		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.1		%
Supply									
Positive	,	V V or CND	Switch ON or	25°C	261/		0.05	0.5	
supply current	l ₊	$V_1 = V_+ \text{ or GND},$	OFF	Full 3.6 V		0.75		0.75	μΑ

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Electrical Characteristics for 2.5-V Supply

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T_A	V ₊	MIN	TYP	MAX	UNIT
Analog Switch								<u>"</u>	
Analog signal range	$V_{\mbox{\scriptsize COM}}, V_{\mbox{\scriptsize NO}}, \ V_{\mbox{\scriptsize NC}}$					0		V ₊	V
Voltage undershoot	V _{IKU}	$0 \text{ mA} \ge (I_{NC}, I_{NO}, \text{ or } I_{CON})$	_A) ≥ -50 mA		2.7 V				V
Peak ON-state	r	$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C	2.3 V		13.9	30	Ω
resistance	r _{peak}	$I_{COM} = -8 \text{ mA},$	See Figure 14	Full	2.5 V			35	12
		V_{NO} or $V_{NC} = 0$,		25°C			6.6	8.5	
ON-state	r _{on}	I _{COM} = 8 mA	Switch ON,	Full	2.3 V			12	Ω
resistance	on	V_{NO} or $V_{NC} = 2.3 V$,	See Figure 14	25°C	2.5 V		8.9	18	32
		$I_{COM} = -8 \text{ mA}$		Full				25	
ON-state				25°C			0.05	0.3	
resistance match between channels	Δr _{on}	V_{NO} or $V_{NC} = 1.6 \text{ V}$, $I_{COM} = -8 \text{ mA}$,	Switch ON, See Figure 14	Full 2.3	2.3 V			0.5	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON,	25°C			5	15	
resistance flatness	r _{on(flat)}	$I_{\text{COM}} = -8 \text{ mA},$	See Figure 14	Full	2.3 V			20	Ω
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0$ to V_+	Switch OFF,	25°C			0.1	10	
OFF leakage current	I _{NO(OFF)}	$V_{COM} = V_{+} \text{ to } 0,$	See Figure 15	Full	2.7 V			100	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0$ to V_+ ,	Switch ON.	25°C	071/		0.1	10	
ON leakage current	I _{NO(ON)}	V _{COM} = Open,	See Figure 16	Full	2.7 V			10	nA
COM		V _{NC} or V _{NO} = Open,	Switch ON,	25°C			0.1	10	
ON leakage current	I _{COM(ON)}	$V_{COM} = 0 \text{ to } V_+,$	See Figure 16	Full	2.7 V			100	nA
Digital Control	Input (IN)								
Input logic high	V _{IH}			Full		$V_+ \times 0.75$		5.5	V
Input logic low	V _{IL}			Full		0		$V_+ \times 0.25$	V
Input leakage	I I	V _I = 5.5 V or 0		25°C 2.7 V 5	10				
current	I_{lH} , I_{lL}	v ₁ = 3.3 v 01 0		Full	2.1 V			20	nA



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Electrical Characteristics for 2.5-V Supply (continued)

 V_{+} = 2.3 V to 2.7 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	IDITIONS	T _A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
		$V_{COM} = V_{+} \text{ or GND},$	$C_L = 50 \text{ pF},$	25°C	2.5 V	2	6.2	9.6	
Turn-on time	t _{ON}	$R_L = 500 \Omega$	See Figure 17	Full	2.3 V to 2.7 V	2		12	ns
		$V_{COM} = V_{+} \text{ or GND},$	C - 50 pF	25°C	2.5 V	1.5	4.5	7.0	
Turn-off time	t _{OFF}	$R_L = 500 \Omega$	C _L = 50 pF, See Figure 17	Full	2.3 V to 2.7 V	1.5		7.5	ns
Output voltage during undershoot	V _{OUTU}	See Figure 24					V _{OH} – 0.3		V
Output voltage during overshoot	V _{OUTO}	See Figure 24					V _{OL} + 0.3	2	V
Break-before-		V - V - V /2	C - 50 pF	25°C	2.5 V	0.5	10	25	
make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2,$ $R_{L} = 50 \Omega,$	C _L = 50 pF, See Figure 18	Full	2.3 V to 2.7 V	0.5		28.5	ns
Charge injection	$Q_{\mathbb{C}}$	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 0.1 nF, See Figure 22	25°C	2.5 V		58		рС
NC, NO OFF capacitance	$\begin{matrix} C_{NC(OFF)}, \\ C_{NO(OFF)} \end{matrix}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		5		pF
NC, NO ON capacitance	$C_{NC(ON)}, \ C_{NO(ON)}$	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 16	25°C	2.5 V		14.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	2.5 V		14.5		pF
Digital input capacitance	C_{l}	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	2.5 V		3.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	2.5 V		367		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 10 MHz,	Switch OFF, See Figure 20	25°C	2.5 V		-60		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, $f = 10 MHz$,	Switch ON, See Figure 21	25°C	2.5 V		-60		dB
Total harmonic distortion	THD	$R_L = 600 \ \Omega,$ $C_L = 50 \ pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.15		%
Supply									
Positive supply current	l ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	2.7 V		50	100 550	nA

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Electrical Characteristics for 1.8-V Supply

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COND	ITIONS	T _A	V.	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}, V_{NC}					0		V ₊	V
Voltage undershoot	V _{IKU}	$0 \ge (I_{NC}, I_{NO}, \text{ or } I_{COM}) \ge$	–50 mA		1.95 V				٧
Peak		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON.	25°C			41.1	60	
ON-state resistance	r _{peak}	$I_{COM} = -4 \text{ mA},$	See Figure 14	Full	1.65 V			120	Ω
		V_{NO} or $V_{NC} = 0$,		25°C			9.2	15	
ON-state	r _{on}	I _{COM} = 4 mA	Switch ON,	Full	1.65 V			15	Ω
resistance	on	V_{NO} or $V_{NC} = 1.65 V$,	See Figure 14	25°C	1.00 1		1.8	40	32
		$I_{COM} = -4 \text{ mA}$		Full				45	
ON-state resistance				25°C			0.1	0.6	
match between channels	Δr_{on}	V_{NO} or $V_{NC} = 1.15 V$, $I_{COM} = -4 \text{ mA}$,	Switch ON, See Figure 14	Full	1.65 V			0.8	Ω
ON-state		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$	Switch ON	25°C			26.5	80	
resistance flatness	r _{on(flat)}	$I_{COM} = -4 \text{ mA},$	See Figure 14	Full	1.65 V			100	Ω
NC, NO	I _{NC(OFF)} ,	V_{NC} or $V_{NO} = 0$ to V_+ ,	Switch OFF,	25°C			0.05	10	
OFF leakage current	I _{NO(OFF)}	$V_{COM} = V_+ \text{ to } 0,$	See Figure 15	Full	1.95 V			100	nA
NC, NO	I _{NC(ON)} ,	V_{NC} or $V_{NO} = 0$ to V_+ ,	Switch ON,	25°C			0.1	10	
ON leakage current	I _{NO(ON)}	V _{COM} = Open,	See Figure 16	Full	1.95 V			100	μA
COM	_	V _{NC} or V _{NO} = Open,	Switch ON,	25°C			0.1	10	
ON leakage current	I _{COM(ON)}	$V_{COM} = 0 \text{ to } V_+,$	See Figure 16	Full	1.95 V			100	nA
Digital Control Ir	put (IN)								
Input logic high	V _{IH}			Full		V ₊ × 0.75		5.5	V
Input logic low	V _{IL}			Full		0		$V_+ \times 0.25$	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	1.95 V		0.05	1 20	nA



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Electrical Characteristics for 1.8-V Supply (continued)

 V_{+} = 1.65 V to 1.95 V, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic	1								
Turn-on time	t	$V_{COM} = V_{+} \text{ or GND},$	C _L = 50 pF,	25°C	1.8 V 1.65 V		9.6	23	ne
rum-on time	t _{ON}	$R_L = 500 \Omega$,	See Figure 17	Full	to 1.95 V			24	ns
				25°C	1.8 V		6.3	10	
Turn-off time	t _{OFF}	$V_{COM} = V_{+} \text{ or GND},$ $R_{L} = 500 \Omega,$	C _L = 50 pF, See Figure 17	Full	1.65 V to 1.95 V			12	ns
Output voltage during undershoot	V _{OUTU}	See Figure 24				,	V _{OH} – 0.3		V
Output voltage during overshoot	V _{OUTO}	See Figure 24				,	V _{OL} + 0.3		V
				25°C	1.8 V	0.5	18	50	
Break-before- make time	t _{BBM}	$V_{NC} = V_{NO} = V_{+}/2,$ $R_{L} = 50 \Omega,$	C _L = 50 pF, See Figure 18	Full	1.65 V to 1.95 V	0.5		55	ns
Charge injection	Q _C	V _{GEN} = 0, R _{GEN} = 0,	C _L = 0.1 nF, See Figure 22	25°C	1.8 V		40		pC
NC, NO OFF capacitance	C _{NC(OFF)} , C _{NO(OFF)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		5.0		pF
NC, NO ON capacitance	C _{NC(ON)} , C _{NO(ON)}	V_{NC} or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 16	25°C	1.8 V		14.5		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	1.8 V		14.5		pF
Digital input capacitance	Cı	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	1.8 V		3.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	1.8 V		369		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 10 MHz,	Switch OFF, See Figure 20	25°C	1.8 V		-60		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 10 MHz,	Switch ON, See Figure 21	25°C	1.8 V		-60		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 23	25°C	1.8 V		0.4		%
Supply				_					
Positive supply current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	1.95 V		0.1	50 400	nA

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PIN DESCRIPTION

PIN NO.	NAME	DESCRIPTION
1	IN1	Digital control to connect COM to NO or NC
2	NO1	Normally open
3	GND	Digital ground
4	NO2	Normally open
5	IN2	Digital control to connect COM to NO or NC
6	COM2	Common
7	NC2	Normally closed
8	V+	Power supply
9	NC1	Normally closed
10	COM1	Common

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V _{COM}	Voltage at COM
V _{NC}	Voltage at NC
V _{NO}	Voltage at NO
r _{on}	Resistance between COM and NC or COM and NO ports when the channel is ON
Δr _{on}	Difference of ron between channels
r _{on(flat)}	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NC(OFF)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the OFF state under worst-case input and output conditions
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
I _{NC(ON)}	Leakage current measured at the NC port, with the corresponding channel (NC to COM) in the ON state and the output (COM) being open
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) being open
I _{COM(ON)}	Leakage current measured at the COM port, with the corresponding channel (NO to COM or NC to COM) in the ON state and the output (NC or NO) being open
V _{IH}	Minimum input voltage for logic high for the control input (IN)
V _{IL}	Minimum input voltage for logic low for the control input (IN)
V _{IN}	Voltage at control input (IN)
$I_{IH},\ I_{IL}$	Leakage current measured at control input (IN)
t _{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning ON.
t _{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog outputs (COM/NC/NO) signal when the switch is turning OFF.
t _{BBM}	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NC, NO, or COM) output. This is measured in coulombs =) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_O$, C_L is the load capacitance and ΔV_O is the change in analog output voltage.
C _{NC(OFF)}	Capacitance at the NC port when the corresponding channel (NC to COM) is OFF
C _{NO(OFF)}	Capacitance at the NO port when the corresponding channel (NC to COM) is OFF
C _{NC(ON)}	Capacitance at the NC port when the corresponding channel (NC to COM) is ON
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NC to COM) is ON
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NC or COM to NO) is ON
C _I	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NC to COM or NO to COM) in the OFF state.



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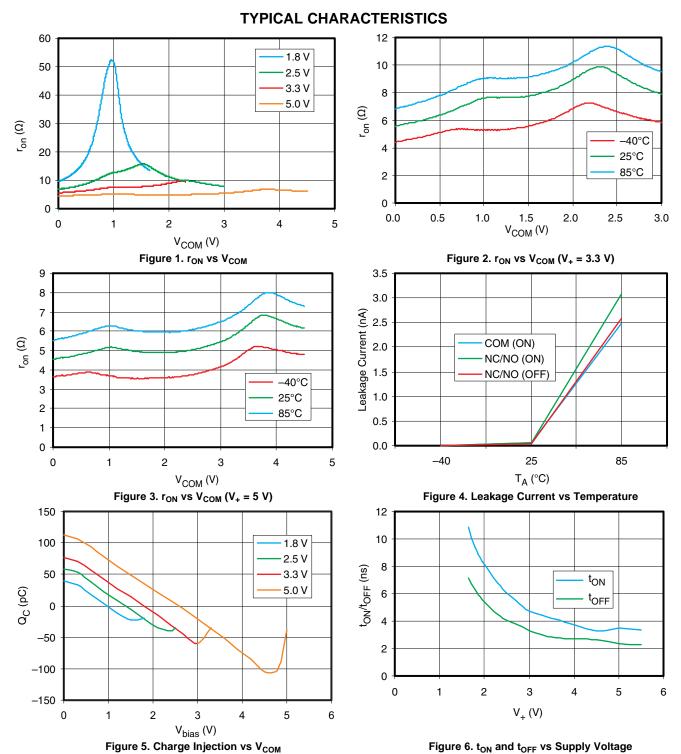
PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
X _{TALK}	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured at a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency where the gain of an ON channel is -3 dB below the dc gain.
THD	Total harmonic distortion is defined as the ratio of the root mean square (RMS) value of the second, third, and higher harmonics to the magnitude of fundamental harmonic.
l+	Static power-supply current with the control (IN) pin at V+ or GND
V _{OUTU}	Output voltage during an undershoot event. This is measured by turning off a specific channel and applying an undershoot voltage at the input of the switch.
V _{OUTO}	Output voltage during an overshoot event. This is measured by turning off a specific channel and applying an overshoot voltage at the input of the switch.

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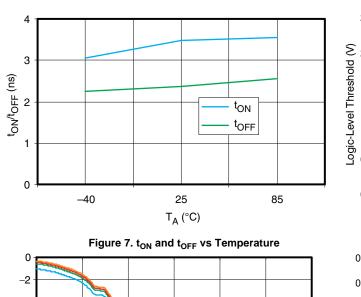
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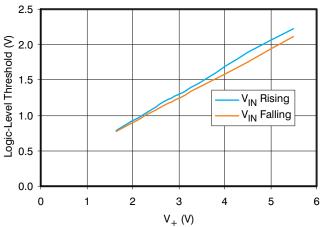


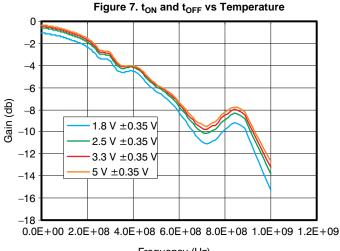


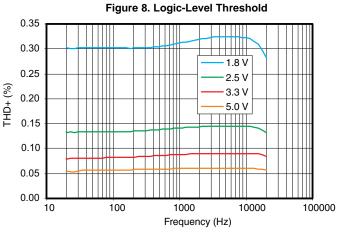
PRODUCT PREVIEW

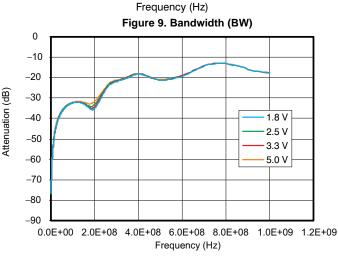
TYPICAL CHARACTERISTICS (continued)











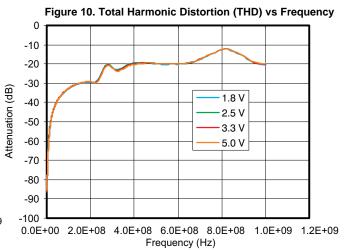


Figure 11. Off Isolation

Figure 12. Crosstalk



TYPICAL CHARACTERISTICS (continued)

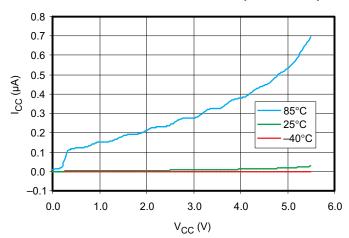


Figure 13. Supply Current vs Supply Voltage

PARAMETER MEASUREMENT INFORMATION

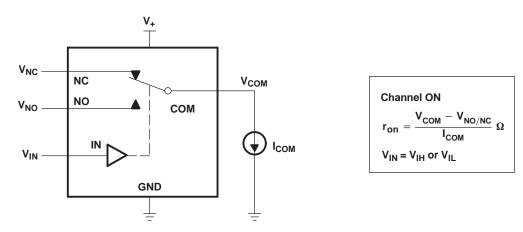


Figure 14. ON-State Resistance (ron)

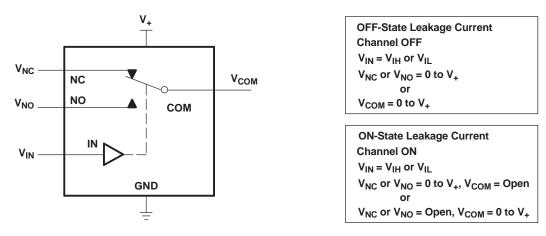


Figure 15. ON- and OFF-State Leakage Current (I_{COM(ON)}, I_{NC(OFF)}, I_{NO(OFF)}, I_{NO(ON)}, I_{NO(ON)})

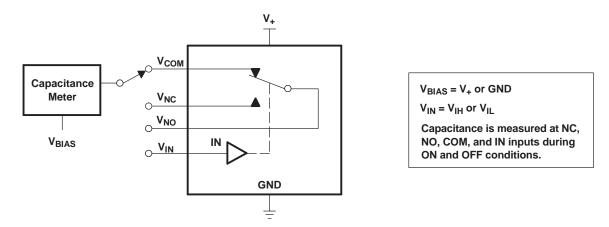
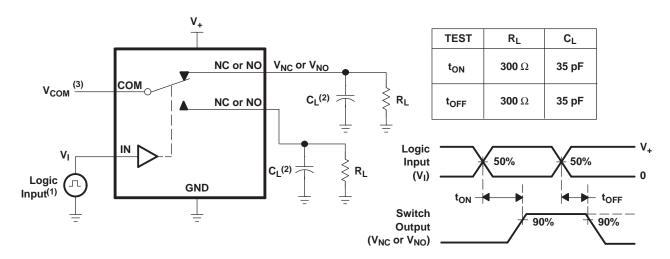


Figure 16. Capacitance (C_{IN}, C_{COM(ON)}, C_{NC(OFF)}, C_{NO(OFF)}, C_{NC(ON)}, C_{NO(ON)})

PRODUCT PREVIEW



PARAMETER MEASUREMENT INFORMATION (continued)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.
- (3) See Electrical Characteristic for V_{COM}.

Figure 17. Turn-On (t_{ON}) and Turn-Off (t_{OFF}) Time

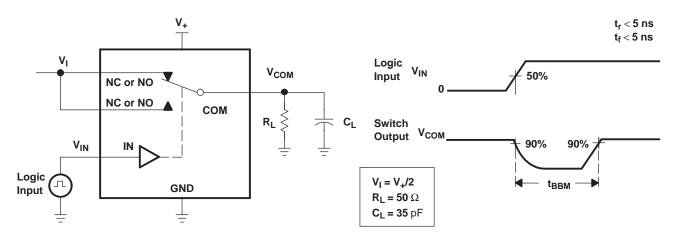


Figure 18. Break-Before-Make (t_{BBM}) Time

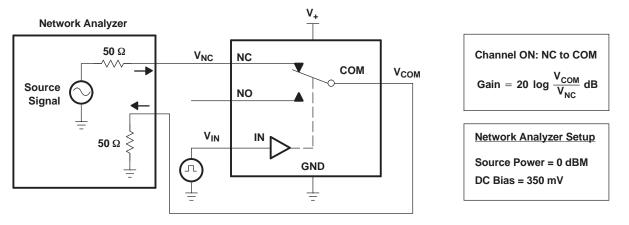


Figure 19. Frequency Response (BW)



PARAMETER MEASUREMENT INFORMATION (continued)

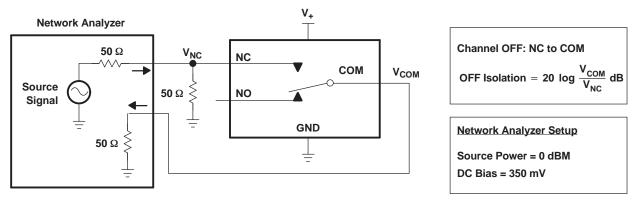


Figure 20. OFF Isolation (O_{ISO})

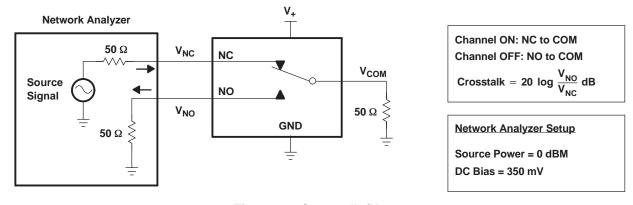


Figure 21. Crosstalk (X_{TALK)}

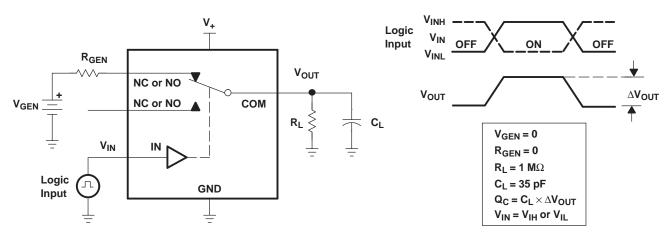


Figure 22. Charge Injection (Q_C)



PARAMETER MEASUREMENT INFORMATION (continued)

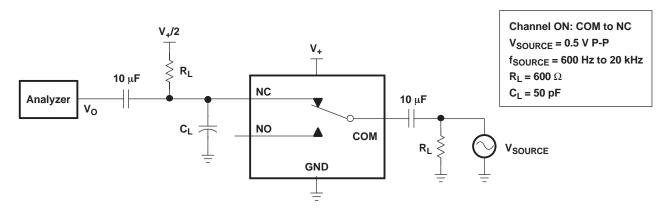


Figure 23. Total Harmonic Distortion (THD)

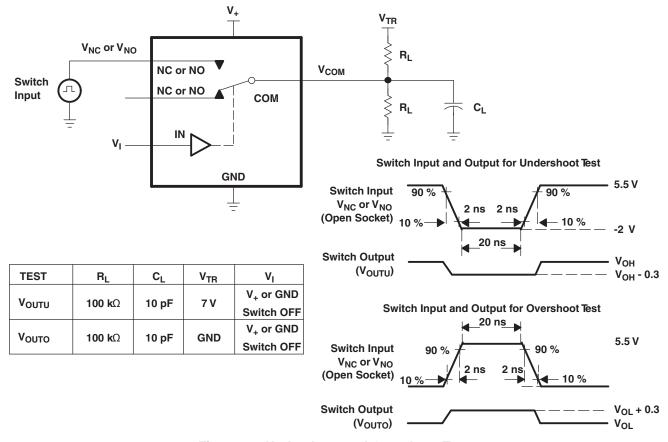


Figure 24. Undershoot and Overshoot Test

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A623157DGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	35R	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A623157DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A623157DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
	TS5A623157DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
ĺ	TS5A623157DGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0



SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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